

Title (en)

METHOD FOR PRODUCING SILICIDED POLYSILICON CONTACTS IN INTEGRATED SEMICONDUCTOR STRUCTURES

Title (de)

VERFAHREN ZUR HERSTELLUNG VON SILIZIERTEN POLYSILIZIUMKONTAKTEN IN INTEGRIERTEN HALBLEITERSTRUKTUREN

Title (fr)

PROCEDE DE REALISATION DE CONTACTS EN SILICIURE DE POLYSILICIUM DANS DES STRUCTURES EN SEMI-CONDUCTEUR INTEGRES

Publication

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Application

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Abstract (en)

[origin: WO0106554A1] The resistance of a polysilicon structure is often reduced by providing it with a silicide layer. However this presents a production problem in terms of only siliconizing certain polysilicon layers. Others, such as those that are to be used for resistors, are not siliconised. The invention therefore provides a simple method for the selective siliconization of polysilicon areas in integrated semiconductor structures.

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IPC 8 full level

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CPC (source: EP KR US)

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Citation (search report)

See references of WO 0106554A1

Citation (examination)

- US 5219768 A 19930615 - OKITA YOSHIHISA [JP]
- BOCK J ET AL: "0.5 /spl mu/m/60 GHz fmax implanted base Si bipolar technology", BIPOLAR/BICMOS CIRCUITS AND TECHNOLOGY MEETING, 1998. PROCEEDINGS OF T HE 1998 MINNEAPOLIS, MN, USA 27-29 SEPT. 1998, PISCATAWAY, NJ, USA,IEEE, US, 27 September 1998 (1998-09-27), pages 160 - 163, XP010318211, ISBN: 978-0-7803-4497-6, DOI: DOI:10.1109/BIPOL.1998.741913

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